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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SD1559

Silicon NPN Triple Diffused

RENESAS

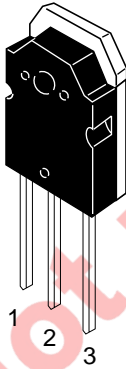
ADE-208-914 (Z)
1st. Edition
September 2000

Application

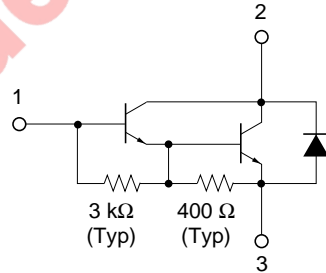
Low frequency power amplifier complementary pair with 2SB1079

Outline

TO-3P



- 1. Base
- 2. Collector (Flange)
- 3. Emitter



Absolute Maximum Ratings (Ta = 25°C)

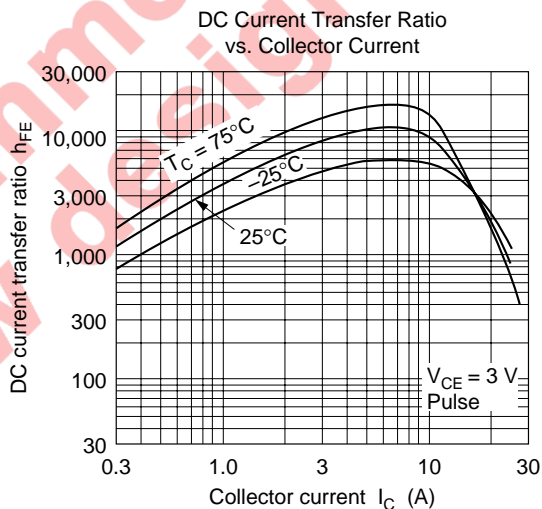
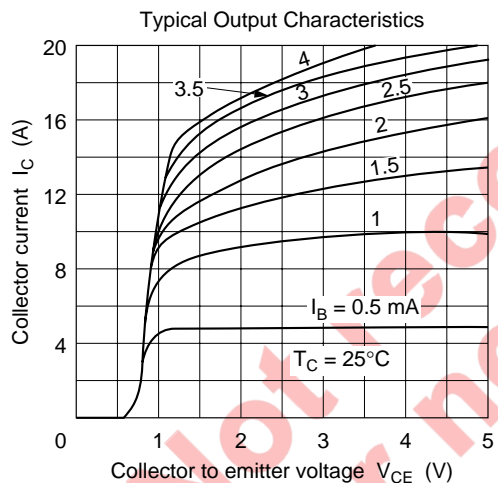
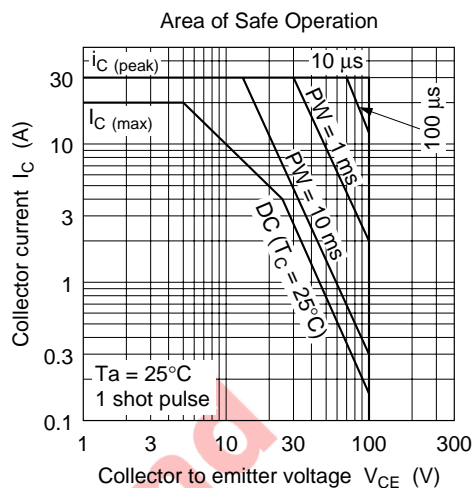
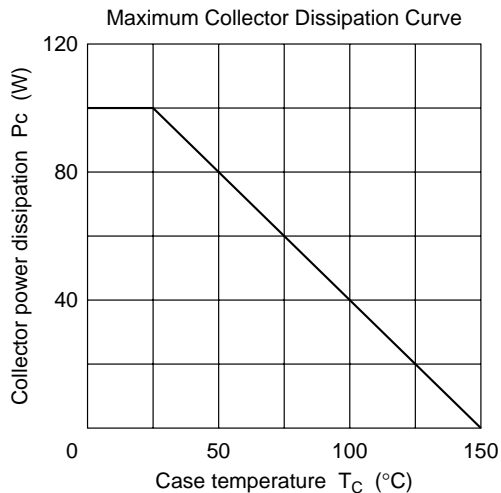
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	100	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	20	A
Collector peak current	$I_{C(peak)}$	30	A
Base current	I_B	3	A
Collector power dissipation	P_C^{*1}	100	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

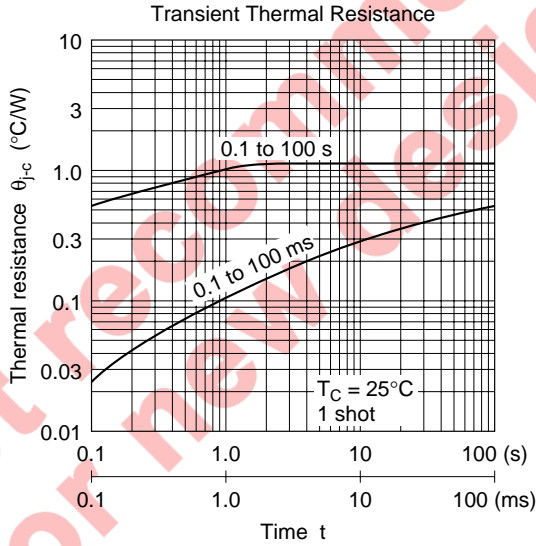
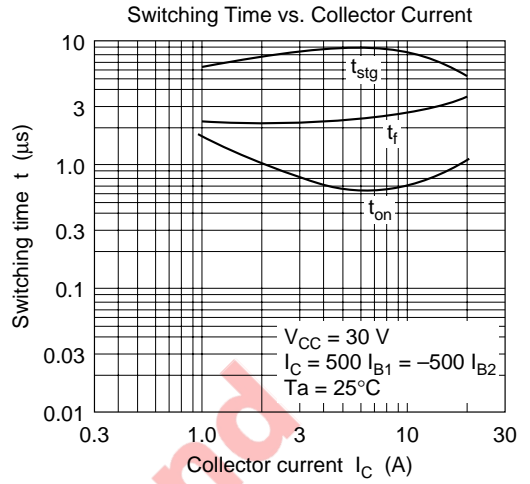
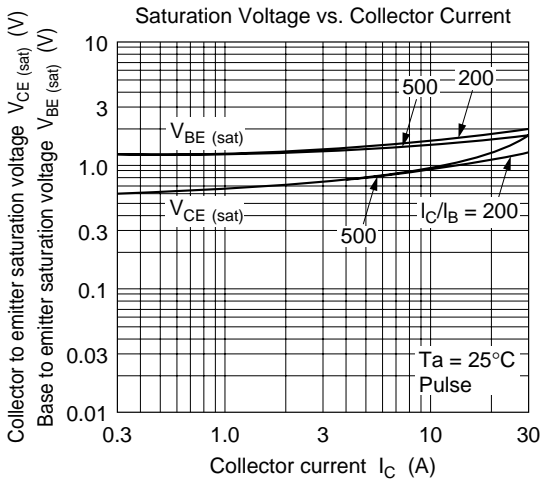
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	100	—	—	V	$I_C = 0.1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	100	—	—	V	$I_C = 25 \text{ mA}, R_{BE} = \infty$
Collector to emitter sustain voltage	$V_{CEO(sus)}$	100	—	—	V	$I_C = 200 \text{ mA}, R_{BE} = \infty^{*1}$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$V_{EB} = 50 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	100	μA	$V_{CB} = 100 \text{ V}, I_E = 0$
	I_{CEO}	—	—	1.0	mA	$V_{CE} = 80 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = 3 \text{ V}, I_C = 10 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	2.0	V	$I_C = 10 \text{ A}, I_B = 20 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2.5	V	
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	—	3.0	V	$I_C = 20 \text{ A}, I_B = 200 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)2}$	—	—	3.5	V	
Turn on time	t_{on}	—	1.0	—	μs	$I_C = 10 \text{ A}, I_{B1} = -I_{B2} = 20 \text{ mA}$
Storage time	t_{stg}	—	9.0	—	μs	
Fall time	t_f	—	3.0	—	μs	

Note: 1. Pulse test.





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